

High Efficiency Thyristor

$$V_{RRM} = 1200\text{ V}$$

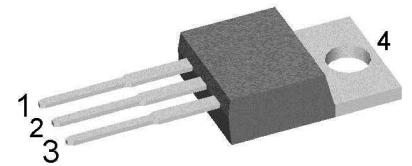
$$I_{TAV} = 15\text{ A}$$

$$V_T = 1.35\text{ V}$$

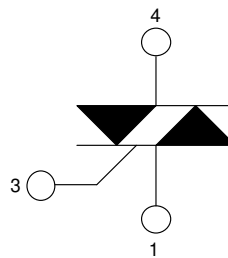
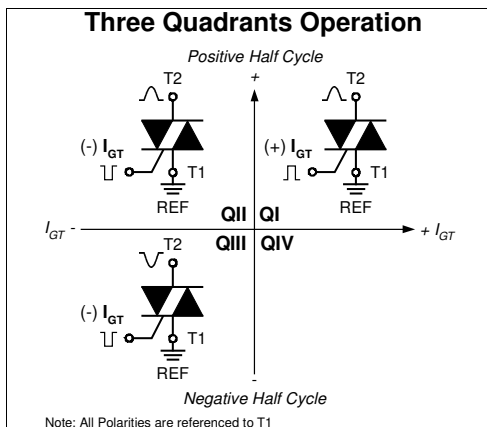
Three Quadrants operation: QI - QIII
 1~ Triac

Part number

CLA30MT1200NPB



Backside: anode/cathode



Features / Advantages:

- Triac for line frequency
- Three Quadrants Operation - QI - QIII
- Planar passivated chip
- Long-term stability of blocking currents and voltages

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- High creepage distance between terminals

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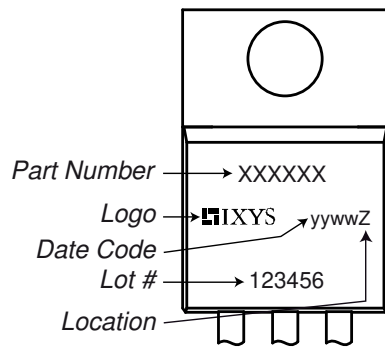


Rectifier			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V
I_{RD}	reverse current, drain current	$V_{R/D} = 1200 V$	$T_{VJ} = 25^{\circ}C$		10	μA
		$V_{R/D} = 1200 V$	$T_{VJ} = 125^{\circ}C$		1.5	mA
V_T	forward voltage drop	$I_T = 15 A$	$T_{VJ} = 25^{\circ}C$		1.35	V
		$I_T = 30 A$			1.68	V
		$I_T = 15 A$	$T_{VJ} = 125^{\circ}C$		1.35	V
		$I_T = 30 A$			1.79	V
I_{TAV}	average forward current	$T_C = 120^{\circ}C$	$T_{VJ} = 150^{\circ}C$		15	A
I_{RMS}	RMS forward current per phase	180° sine			33	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		0.89	V
r_T	slope resistance				30	m Ω
R_{thJC}	thermal resistance junction to case				0.95	K/W
R_{thCH}	thermal resistance case to heatsink			0.5		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		130	W
I_{TSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		170	A
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		185	A
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}C$		145	A
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		155	A
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		145	A ² s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		140	A ² s
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}C$		105	A ² s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		100	A ² s
C_J	junction capacitance	$V_R = 400 V \quad f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		9	pF
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 150^{\circ}C$		5	W
		$t_p = 300 \mu s$			1	W
P_{GAV}	average gate power dissipation				0.2	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 150^{\circ}C; f = 50 \text{ Hz}$	repetitive, $I_T = 45 A$		150	A/ μs
		$t_p = 200 \mu s; di_G/dt = 0.3 A/\mu s;$ $I_G = 0.3 A; V = \frac{2}{3} V_{DRM}$	non-repet., $I_T = 15 A$		500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}C$		500	V/ μs
		$R_{GK} = \infty$; method 1 (linear voltage rise)				
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		1.3	V
			$T_{VJ} = -40^{\circ}C$		1.6	V
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		± 40	mA
			$T_{VJ} = -40^{\circ}C$		± 60	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}C$		0.2	V
I_{GD}	gate non-trigger current				± 1	mA
I_L	latching current	$t_p = 10 \mu s$	$T_{VJ} = 25^{\circ}C$		70	mA
		$I_G = 0.3 A; di_G/dt = 0.3 A/\mu s$				
I_H	holding current	$V_D = 6 V \quad R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		50	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	μs
		$I_G = 0.3 A; di_G/dt = 0.3 A/\mu s$				
t_q	turn-off time	$V_R = 100 V; I_T = 15 A; V = \frac{2}{3} V_{DRM}$ $di/dt = 10 A/\mu s \quad dv/dt = 20 V/\mu s \quad t_p = 200 \mu s$	$T_{VJ} = 125^{\circ}C$		150	μs



Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			35	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				2		g
M_D	mounting torque		0.4		0.6	Nm
F_C	mounting force with clip		20		60	N

Product Marking



Part description

- C = Thyristor (SCR)
- L = High Efficiency Thyristor
- A = (up to 1200V)
- 30 = Current Rating [A]
- MT = 1~ Triac
- 1200 = Reverse Voltage [V]
- N = Three Quadrants operation: QI - QIII
- PB = TO-220AB (3)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CLA30MT1200NPB	CLA30MT1200NPB	Tube	50	517031

Similar Part	Package	Voltage class
CLA30MT1200NPZ	TO-263AB (D2Pak) (2HV)	1200

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}C$

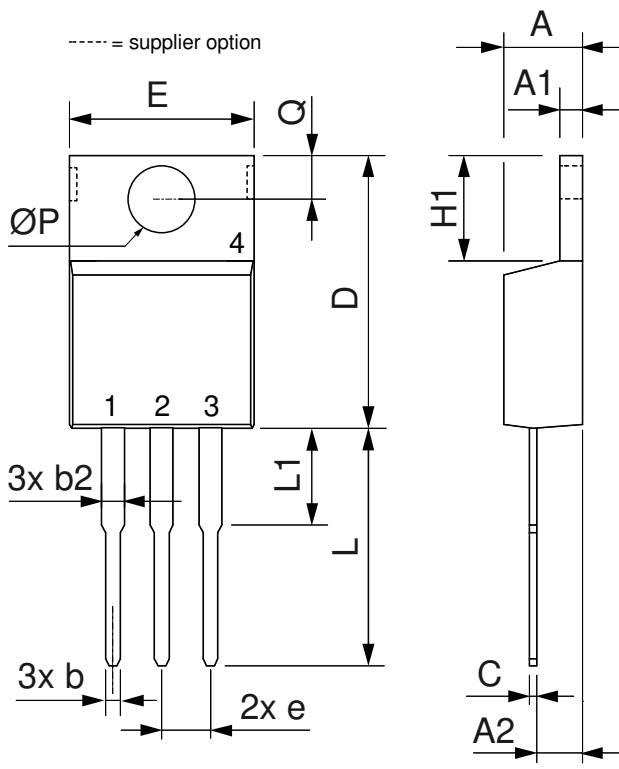


Thyristor

$V_{0\ max}$	threshold voltage	0.89	V
$R_{0\ max}$	slope resistance *	27	mΩ



Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	2.54	BSC	0.100	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125



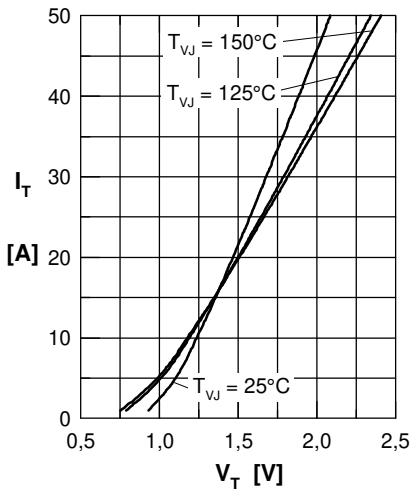
Thyristor


Fig. 1 Forward characteristics

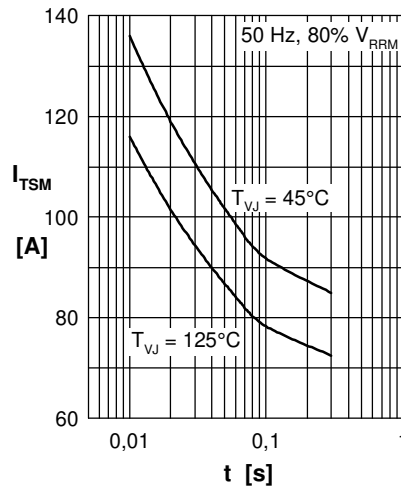


Fig. 2 Surge overload current

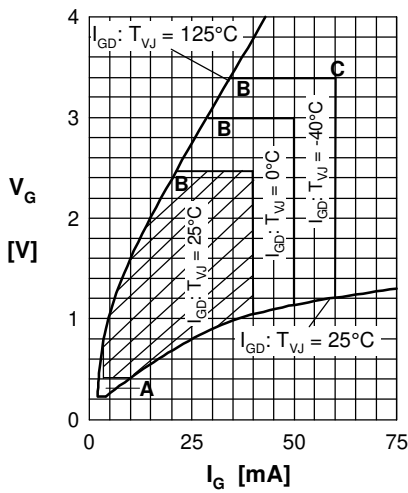

 Fig. 3 I^2t versus time (1-10 ms)


Fig. 4 Gate trigger characteristics

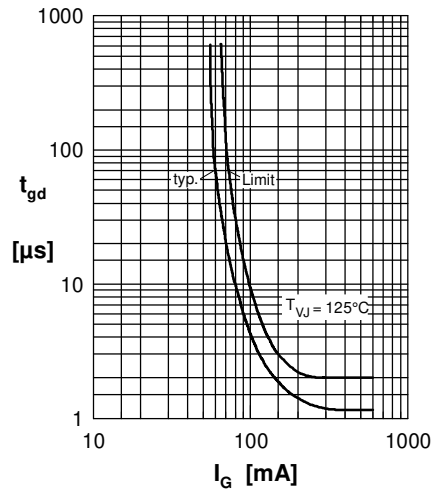


Fig. 5 Gate controlled delay time



Fig. 6 Max. forward current at case temperature

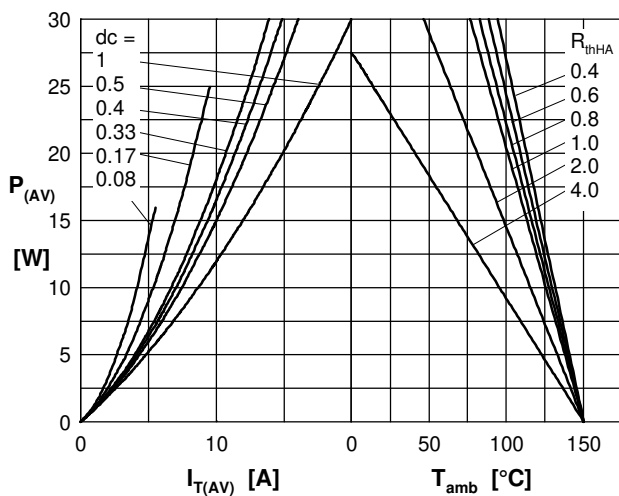
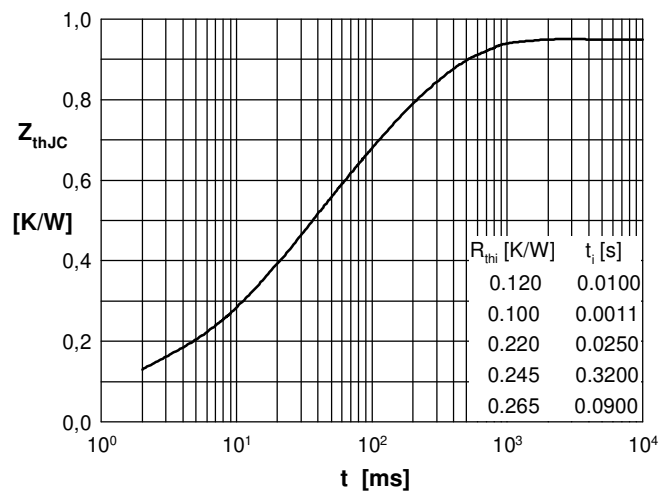

 Fig. 7a Power dissipation versus direct output current
 Fig. 7b and ambient temperature


Fig. 8 Transient thermal impedance

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

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